

# SOT223 NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

## FZT696B

ISSUE 4 – FEBRUARY 1997

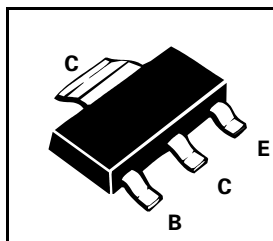
### FEATURES

- \* 250 Volt  $V_{CEO}$
- \* Gain of 500 at  $I_C=100\text{mA}$
- \* Very low saturation voltage

### APPLICATIONS

- \* Darlington replacement
- \* Battery powered circuits

PARTMARKING DETAIL – FZT696B



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	180	V
Collector-Emitter Voltage	$V_{CEO}$	180	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Peak Pulse Current	$I_{CM}$	1	A
Continuous Collector Current	$I_C$	0.5	A
Power Dissipation at $T_{amb}=25^\circ\text{C}$	$P_{tot}$	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	180			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	180			V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$			0.1	$\mu\text{A}$	$V_{CB}=140\text{V}$
Emitter Cut-Off Current	$I_{EBO}$			0.1	$\mu\text{A}$	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.2 0.2 0.25	V	$I_C=50\text{mA}, I_B=0.5\text{mA}^*$ $I_C=100\text{mA}, I_B=2\text{mA}^*$ $I_C=200\text{mA}, I_B=5\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	$I_C=200\text{mA}, I_B=5\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			0.9	V	$I_C=200\text{mA}, V_{CE}=5\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	500 150				$I_C=100\text{mA}, V_{CE}=5\text{V}^*$ $I_C=200\text{mA}, V_{CE}=5\text{V}^*$
Transition Frequency	$f_T$	70			MHz	$I_C=50\text{mA}, V_{CE}=5\text{V}$ $f=50\text{MHz}$
Input Capacitance	$C_{ibo}$		200		pF	$V_{EB}=0.5\text{V}, f=1\text{MHz}$
Output Capacitance	$C_{obo}$		6		pF	$V_{CE}=10\text{V}, f=1\text{MHz}$
Switching Times	$t_{on}$ $t_{off}$		80 4400		ns ns	$I_C=100\text{mA}, I_{B1}=10\text{mA}$ $I_{B2}=10\text{mA}, V_{CC}=50\text{V}$

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

Spice parameter data is available upon request for this device

# FZT696B

## TYPICAL CHARACTERISTICS

